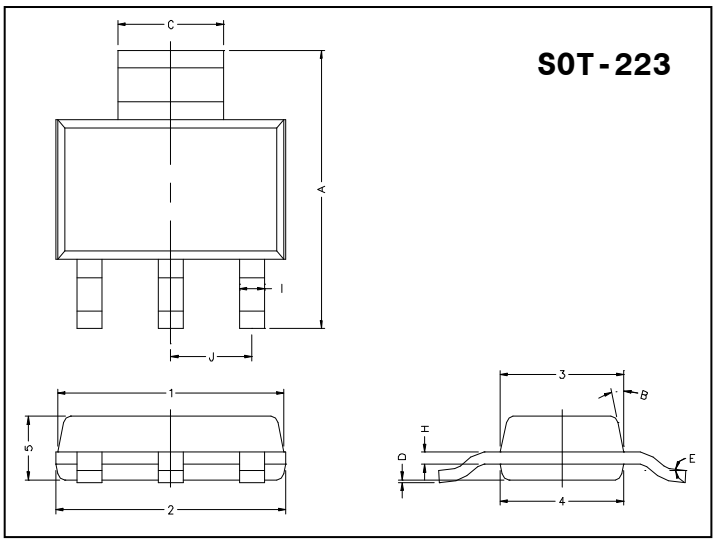
GL5401

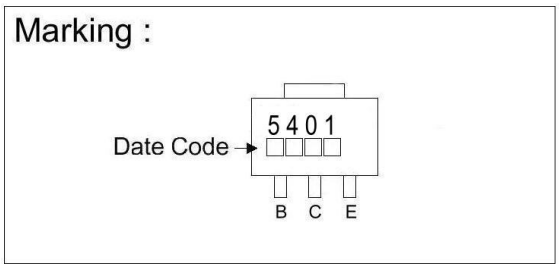
PNP EPITAXIAL PLANAR TRANSISTOR

Description

The GL5401 is designer for general purpose applications requiring high breakdown voltages.

Package Dimensions





REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	6.70	7.30	B	13°TYP.	
C	2.90	3.10	J	2.30 REF.	
D	0.02	0.10	1	6.30	6.70
E	0°	10°	2	6.30	6.70
I	0.60	0.80	3	3.30	3.70
H	0.25	0.35	4	3.30	3.70
			5	1.40	1.80

Absolute Maximum Ratings at Ta = 25℃

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	℃
Storage Temperature	Tstg	-55 ~ +150	℃
Collector to Base Voltage	VCBO	-160	V
Collector to Emitter Voltage	VCEO	-150	V
Emitter to Base Voltage	VEBO	-5	V
Collector Current	IC	-600	mA
Total Power Dissipation	PD	1.5	W

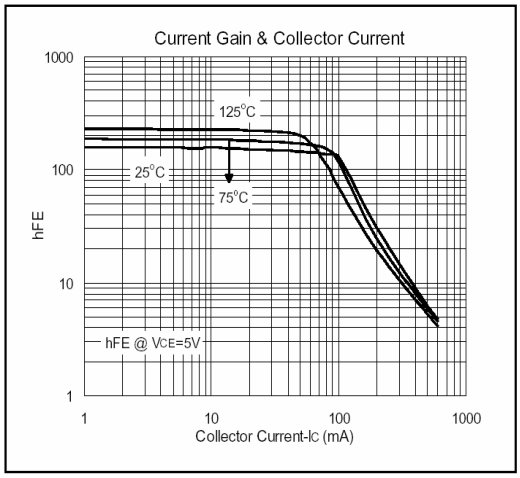
Characteristics at Ta = 25℃

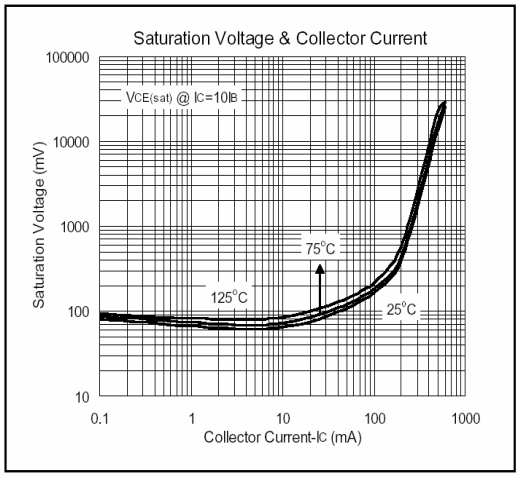
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	-160	-	-	V	IC=-100uA, IE =0
BVCEO	-150	-	-	V	IC=-1mA, IB=0
BVEBO	-5	-	-	V	IE=-10uA, IC=0
ICBO	-	-	-50	nA	VCB=-120V , IE=0
IEBO	-	-	-50	nA	VEB=-3V , IC=0
VCE(sat)1	-	-	-200	mV	IC=-10mA, IB=-1mA
VCE(sat)2	-	-	-500	mV	IC=-50mA, IB=-5mA
VBE(sat)1	-	-	-1	V	IC=-10mA, IB=-1mA
VBE(sat)2	-	-	-1	V	IC=-50mA, IB=-5mA
hFE1	50	-	-		VCE=-5V, IC=-1mA
hFE2	80	160	400		VCE=-5V, IC=-10mA
hFE3	50	-	-		VCE=-5V, IC=-50mA
fT	100	-	300	MHz	VCE=-10V, IC=-10mA, f=100MHz
Cob	-	-	6	pF	VCB=-10V, IE=0, f=1MHz

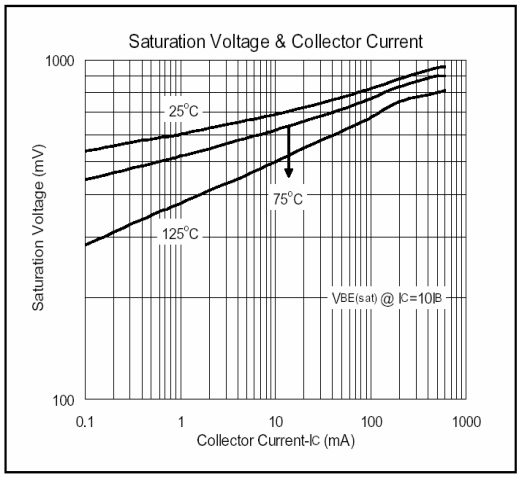
Classification Of hFE

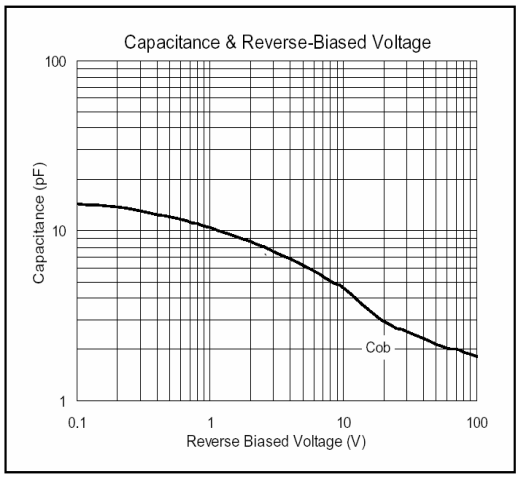
Rank	A	N	C
Range	80 - 200	100 - 240	160 - 400

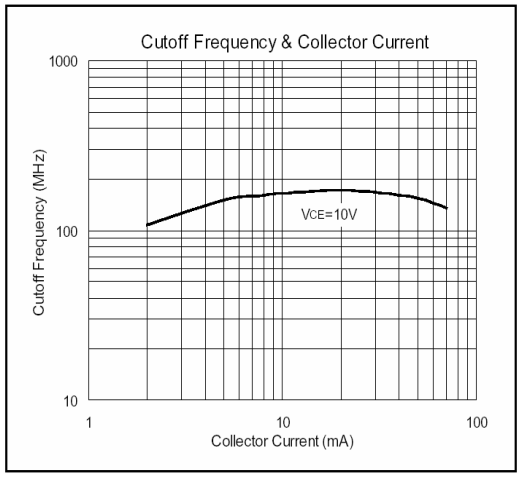
Characteristics Curve











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